

# Description

The 9926A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

# **General Features**

VDS = 20V ID = 6A

 $R_{DS(ON)} < 25m\Omega @ V_{GS}=4.5V$ 

# Application

Battery protection

Load switch

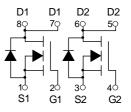
Uninterruptible power supply

# **Package Marking and Ordering Information**

Product ID		Pack	Marking		Qty(PCS)		
9926A		SOP-8	9926 XXX YYYY		3000		
Absolute Max	cimum R	atings@T <sub>j</sub> =25	5°C(unless otherwis	e specifie	d)		
Symbol		Para	ameter	R	Rating		
Vds	Drain-S	ource Voltage		20		V	
Vgs	Gate-Se	Gate-Source Voltage			<u>+</u> 12		
I₀@T₄=25°C	Drain C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>			6		
D@T <sub>A</sub> =70°C	Drain C	Drain Current, V <sub>GS</sub> @ 4.5V <sup>3</sup>			4.8		
DM	Pulsed	Pulsed Drain Current <sup>1</sup>		26		А	
P₀@T₄=25℃	Total Po	Total Power Dissipation			2		
	Linear Derating Factor			0.016		W/°C	
Тѕтс	Storage	e Temperature Ra	ange	-55	to 150	°C	
TJ	Operati	Operating Junction Temperature Range		-55 to 150		°C	
Rthj-a		Maximum Thermal Resistance, Junction- ambient <sup>3</sup>		62.5		°C/W	



SOP-8



#### Dual N-Channel MOSFET



# Electrical Characteristics@Tj=25°C(unless otherwise specified)

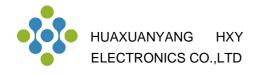
				,	r	r
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Rds(on)	Static Drain-Source On- Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	21	25	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	32	45	mΩ
VGS(th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA V <sub>DS</sub> =10V, I <sub>D</sub> =6A		1.2	3	V
<b>g</b> fs	Forward Transconductance			6	-	S
Idss	Drain-Source Leakage Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	25	uA
	Drain-Source Leakage Current (Tj=70°C)	V <sub>DS</sub> =20V ,V <sub>GS</sub> =0V	-	-	250	uA
Igss	Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =6A	-	11	17.6	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =16V	-	1.1	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	4.1	-	nC
td(on)	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =10V	-	4.2	-	ns
tr	Rise Time	I <sub>D</sub> =1A	-	9	-	ns
td(off)	Turn-off Delay Time	R <sub>G</sub> =3.3Ω,V <sub>GS</sub> =10V R <sub>D</sub> =10Ω	-	23	-	ns
t <sub>f</sub>	Fall Time		-	3.5	-	ns
Ciss	Input Capacitance		-	570	910	pF
Coss	Output Capacitance	V <sub>GS</sub> =0V	-	90	-	pF
Crss	Reverse Transfer Capacitance	V <sub>DS</sub> =20V f=1.0MHz	-	85	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1.6	2.4	Ω
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	Is=1.7A, V <sub>GS</sub> =0V	-	-	1.2	V
trr	Reverse Recovery Time <sup>2</sup>	Is=6A, V <sub>GS</sub> =0V,	-	21	-	ns
Qrr	Reverse Recovery Charge	dl/dt=100A/µs	-	14	-	nC

### Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t  $\leq$ 10sec ; 135 °C/W when mounted on Min. copper pad.



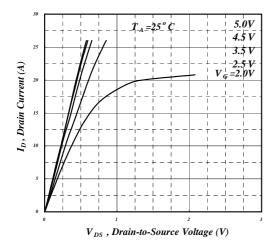


Fig 1. Typical Output Characteristics

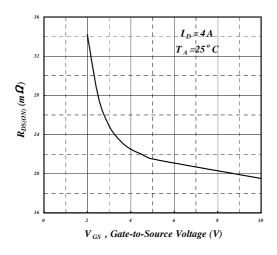


Fig 3. On-Resistance v.s. Gate Voltage

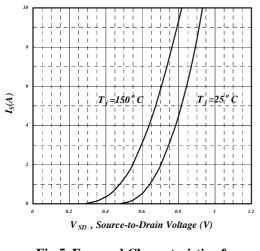


Fig 5. Forward Characteristic of Reverse Diode

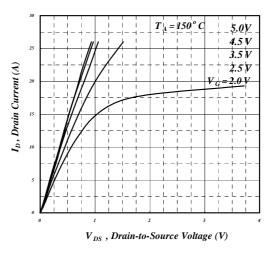


Fig 2. Typical Output Characteristics

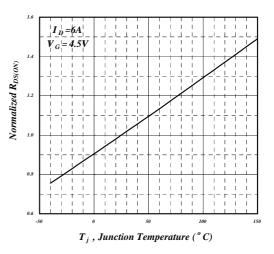


Fig 4. Normalized On-Resistance v.s. Temperature

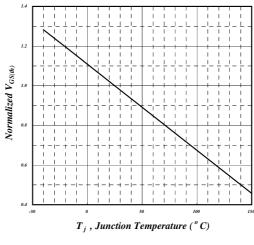
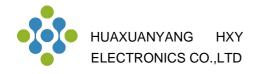


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



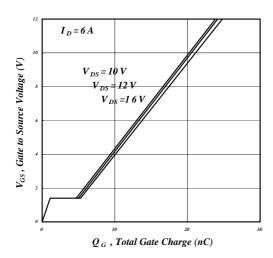


Fig 7. Gate Charge Characteristics

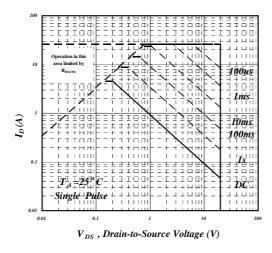


Fig 9. Maximum Safe Operating Area

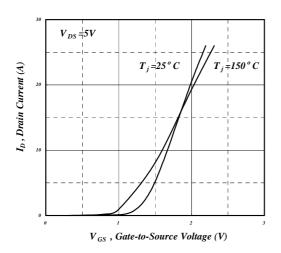


Fig 11. Transfer Characteristics

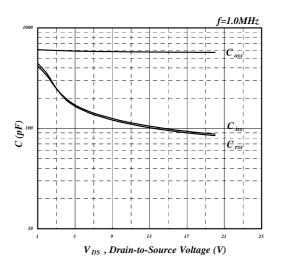


Fig 8. Typical Capacitance Characteristics

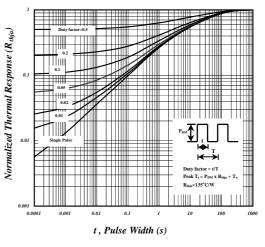


Fig 10. Effective Transient Thermal Impedance

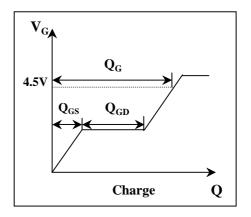
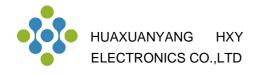
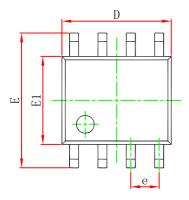
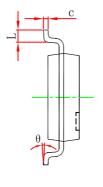


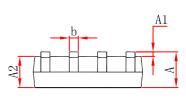
Fig 12. Gate Charge Waveform



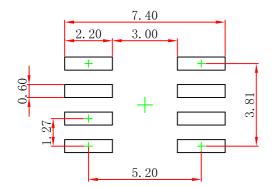
# SOP-8 Package Outline Dimensions







Symbol	Dimensions In	Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (	BSC)	0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



Note: 1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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